# RENESAS BCR10PM-12LG

Triac Medium Power Use

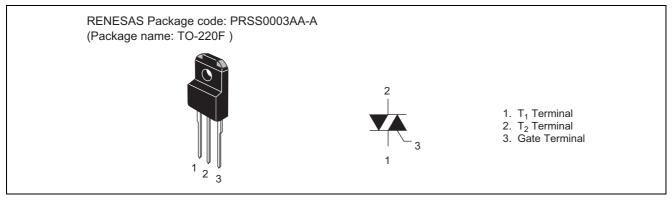
> REJ03G1509-0200 Rev.2.00 Jun 28, 2007

# Features

- I<sub>T (RMS)</sub> : 10 A
- V<sub>DRM</sub> : 600 V
- I<sub>FGTI</sub>, I<sub>RGTI</sub>, I<sub>RGT III</sub>: 30 mA
- V<sub>iso</sub> : 2000 V

- The Product guaranteed maximum junction temperature 150°C
- Insulated Type
- Planar Type
- UL Recognized : Yellow Card No. E223904 File No.E80271

# Outline



# Applications

Switching mode power supply, light dimmer, electronic switch, hair dryer, Television, Stereo system, refrigerator, Washing machine, infrared kotatsu, and carper, small motor controller, SS relay, solenoid driver, copying machine, electric tool, electric heater control, and other general purpose control applications

Parameter	Symbol	Voltage class	Unit
Falailletei	Symbol	12	
Repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DRM</sub>	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DSM</sub>	720	V

### BCR10PM-12LG

Parameter	Symbol	Ratings	Unit	Conditions	
RMS on-state current	I <sub>T (RMS)</sub>	10	A	Commercial frequency, sine full wave 360° conduction, Tc = 103° C	
Surge on-state current	I <sub>TSM</sub>	100	A	60Hz sinewave 1 full cycle, peak value, non-repetitive	
I <sup>2</sup> t for fusion	l <sup>2</sup> t	41.6	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	
Peak gate power dissipation	P <sub>GM</sub>	5	W		
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W		
Peak gate voltage	V <sub>GM</sub>	10	V		
Peak gate current	I <sub>GM</sub>	2	А		
Junction Temperature	Tj	-40 to +150	°C		
Storage temperature	Tstg	-40 to +150	°C		
Mass	_	2.0	g	Typical value	
Isolation voltage	V <sub>iso</sub>	2000	V	Ta = 25°C, AC 1 minute, T <sub>1</sub> • T <sub>2</sub> • G terminal to case	

Notes: 1. Gate open.

# **Electrical Characteristics**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	—	—	2.0	mA	Tj = 150°C, V <sub>DRM</sub> applied
On-state voltage		V <sub>TM</sub>	—	—	1.5	V	Tc = 25°C, $I_{TM}$ = 15 A, instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I $V_{FGTI}$ — — 1.5 V $Tj = 25^{\circ}C, V_{D} = 6 V$	$Tj = 25^{\circ}C, V_{D} = 6 V, R_{L} = 6 \Omega,$					
	II	$V_{RGTI}$	—	—	1.5	V	$R_G = 330 \Omega$
	III	V <sub>RGTIII</sub>	—	—	1.5	V	
Gate trigger curent <sup>Note2</sup>	Ι	I <sub>FGTI</sub>	—	—	30	mA	$\label{eq:gamma} \begin{array}{l} Tj = 25^\circC, \ V_D = 6 \ V, \ R_L = 6 \ \Omega, \\ R_G = 330 \ \Omega \end{array}$
	II	I <sub>RGTI</sub>	—	—	30	mA	
	III	I <sub>RGTIII</sub>	—	—	30	mA	
Gate non-trigger voltage		$V_{GD}$	0.2/0.1			V	$Tj = 125^{\circ}C/150^{\circ}C, V_{D} = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>			4.1	°C/W	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutation voltage <sup>Note4</sup>		(dv/dt)c	10/1	—	—	V/µs	Tj = 125°C/150°C

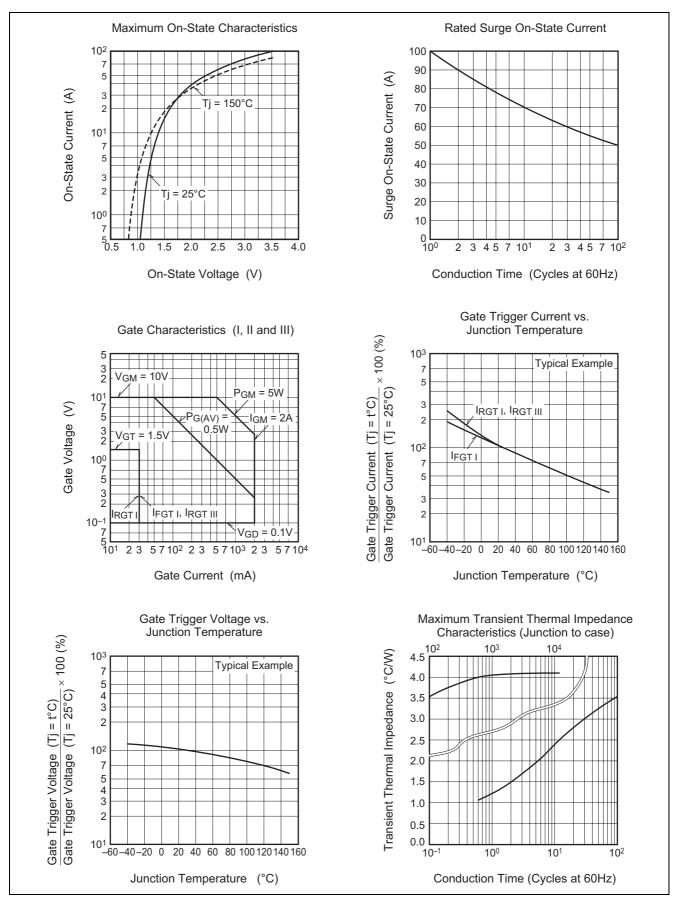
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance  $R_{th (c-f)}$  in case of greasing is 0.5°C/W.

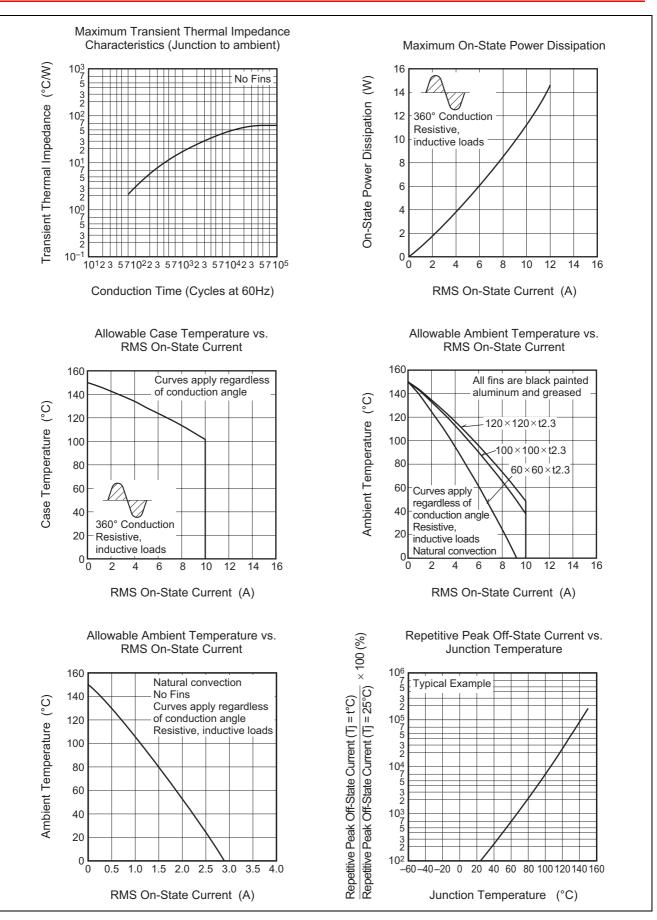
4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C/150°C	Supply Voltage → Time		
<ol> <li>Rate of decay of on-state commutating current (di/dt)c = -5.0 A/ms</li> </ol>	Main Current → Time		
3. Peak off-state voltage V <sub>D</sub> = 400 V	Main VoltageTime (dv/dt)cV		

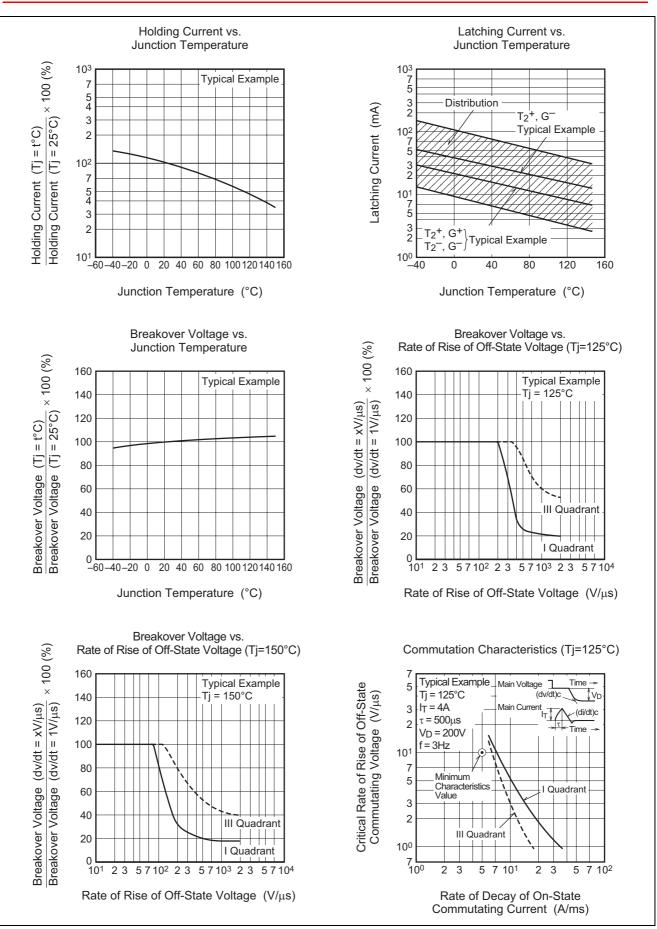
# **Performance Curves**



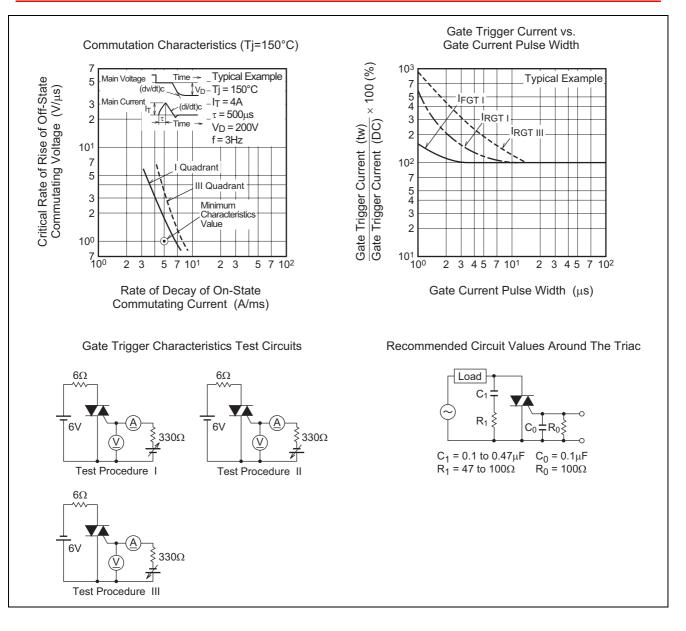
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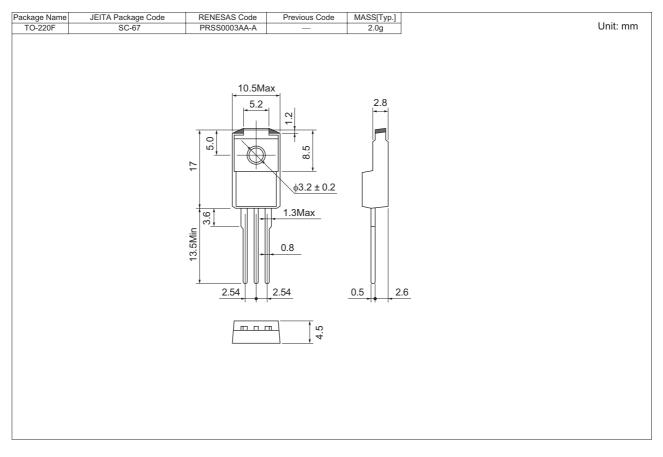
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# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR10PM-12LG
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR10PM-12LG-A8

Note : Please confirm the specification about the shipping in detail.

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